TC5588P/J-15,-20,-25,-35

8,192 WORD × 8 BIT CMOS STATIC RAM

DESCRIPTION

The TC5588P/J is a 65,536 bits high speed static random access memory organized as 8,192 words by 8 bits using CMOS technology, and operated from a single 5-volt supply. Toshiba's CMOS technology and advanced circuit from provides high speed feature.

The TC5588P/J has low power feature with device control using Chip Enable (CEI/CE2), and has Output Enable Input (OE) for fast memory access. Also the device power at memory access is reduced by automatic power down circuit form.

The TC5588P/J is suitable for use in cache memory where high speed is required, and high speed storage. All Inputs and Outputs are directly TTL compatible.

The TC5588P/J is moulded in 28 pin standard DIP and SOJ with 300 mil width for high density surface assembly.

FEATURES

Fast access time:

TC5588P/J-15 15ns (MAX.) TC5588P/J-20 20ns (MAX.) 25ns (MAX.) TC5588P/J-25 TC5588P/J-35 35ns (MAX.)

Low power dissipation:

135mA (MAX.) TC5588P/J-15 Operation TC5588P/J-20 115mA (MAX.)

TC5588P/J-25 115mA (MAX.) TC5588P/J-35 115mA (MAX.)

1mA (MAX.) Standby

5V single power supply: 5V ± 10%

Fully static operation

Directly TTL compatible: All Input and Output

Output buffer control: OE

Package

TC5588P: DIP28-P-300B TC5588J: SOJ28-P-300A

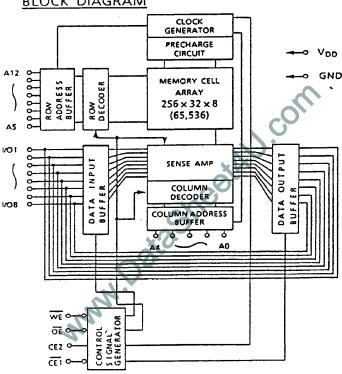
PIN CONNECTION

TC5588	P	TC55	1881
A12 0 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	28 VOO 27 WE 26 CE2 25 A8 24 A9 23 A11 22 OE 21 A10 20 CE1 19 I/O8 18 I/O7 17 I/O6 16 I/O5	N.C. 1 1 1 2 2 A 7 1 3 A 6 1 4 A 5 1 5 A 4 1 6 A 7 A 2 1 8 A 1 1 9 A A 1 1 1 1 1 1 1 1 1 1 1 1 1 1	28] V _{OO} 27] WE 26] CE2 25] A8 24] A9 23] A11 22] OE 21] A10 20] CE1 19] VO8 18] VO7 17] VO6 16] I/O5 15] VO4
(DIP)		(SO	J)

PIN NAMES

A0~A12	Address Inputs
1/01~1/08	Data Inputs/Outputs
CET, CE2	Chip Enable Inputs
WE	Write Enable Input
ठह	Output Enable Input
Voo	Power (+ 5V)
GND	Ground
N.C.	No Connection

BLOCK DIAGRAM



AXIMUM RATINGS

ANTON IN	ITEM	RATING	UNIT
SYMBOL		-0.5~7.0	V
V ₀₀	Power Supply Voltage	- 2.0~7.0	V
V _{IN}	Input Voltage	-0.5~V _{DD} +0.5	V
Vout	Output Voltage	1.0	w
Po	Power Dissipation	260 - 10	°C · sec
Tsolder	Soldering Temperature - Time	- 65~150	°C
Tstrg	Storage Temperature	-10~85	°C
Topr	Operating Temperature		

TO RECOMMENDED OPERATING CONDITIONS (Ta = 0~70°C)

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	ואט
31111000	Power Supply Voltage	4.5	5.0	5.5	V
V ₀₀		2.2	-	V _{DD} + 0.5	v
V _{IH}	Input High Voltage Input Low Voltage	*-3.0	-	0.8	V

^{*} Pulse width \leq 10ns, DC: -0.5V (min)

CC CHARACTERISTICS (Ta = 0~70°C, VDD = 5V ± 10%)

SYMBOL	PARAMETER	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
31101000		V _{IN} = 0~V _{DD}		-	-	± 1	μA
In	Input Leakage Current			- 4	_	-	mA
он	Output High Current	V _{OH} = 2.4V		8	_	_	mΑ
lou	Output Low Current	V _{OL} = 0.4V				 	<u> </u>
Ito	Output Leakage Current	CET = V _{IH} or CE2 = V _{IL} or WE = V _{IL} or OE = V _{IH} , V _{OUT} = 0~V _{DD}		-	-	±1	μΑ
		V _{DO} = 5.5V tcycle = Min cycle	- 15	-		135	
		CET = VIL and CE2 = VIH	- 20				m.A
I _{D00}	Operating Current	Other Inputs = VIH/VIL	- 25	_	ا	115	""
		I _{OUT} = 0mA	- 35				
		V _{DD} = 5.5V tcycle = Min cycle					
		CET = VIH or CE2 = VIL		-	-	25	
loosi	Standby Current	Other Inputs = VIH/VIL			ļ		- m
	- Standby Current	$\overline{CE1} = V_{OD} - 0.2V$ or $CE2 = 0.2V$			_	1	
IDDS2 *		Other Inputs = $V_{DD} - 0.2V$ or 0.2V		_	-	·	

^{*:} In standby mode with $\overline{CE1} \ge V_{DD} - 0.2V$, these specification limits are guaranteed under the condition of $\overline{CE2} \ge V_{DD} - 0.2V$ or $CE2 \le 0.2V$.

TAPACITANCE (Ta = 25°C, f = 1.0MHz)

APACITANCE	(1a - 2) C, 1 - 1:0171127			
SYMBOL	PARAMETER	TEST CONDITION '	MAX.	UNIT
3110000	Laura Canaditanca	V _{IN} = GND	5	pF
CiN	Input Capacitance	V _{OUT} = GND	7 .	pF
Cour	Output Capacitance	V001 = 0.10		

NOTE: This parameter periodically sampled is not 100% tested.

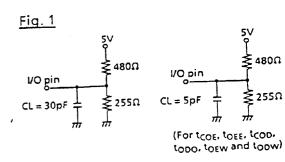
AC CHARACTERISTICS (Ta = $0 \sim 70^{\circ}$ C (1), $V_{DD} = 5V \pm 10\%$)

EAD CYCL	E		0041.15	TC558	8P/J-20	TC558	8P/J-25	TC558	8P/J-35	บทเ
			8P/J-15	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	UNI
SYMBOL	PARAMETER	MIN.	MAX.		 	25	_	35	_	
† _{RC}	Read Cycle Time	15		20	<u> </u>	23	25		35	ļ
	Address Access Time		15		20	<u> </u>	 		35	
t _{ACC}	CET Access Time		15		20	<u> </u>	25		35	1
tco1	CE2 Access Time		15		20		25			ł
tcoz	OE Access Time	-	9		10		12	<u> </u>	12	-
^t OE	Output Data Hold Time From Address	5	_	5	_	5	-	5	-	n:
tон	Change	ļ	 	5	+	5	_	5	_] '"
t _{COE}	Output Enable Time from CE1 or CE2	5	 			 	6	_	6	1
tcop	Output Disable Time from CE1 or CE2	<u> -</u>	6	 - -	6		<u> </u>	0	 _	1
TOEE	Output Enable Time from OE	0	 -	0	-	0	5	 _	5	1
topo	Output Disable Time from OE	<u> </u>	5	<u> </u>	5	 -		0	 _	1
tpU	Chip Selection to Power Up Time	0	 -	0	 -		-	+		1
t _{PD}	Chip Deselection to Power Down	_	15		20		25		35	

RITE CYC	LE	I TOESR	8P/J-15	TC558	8P/J-20	TC558	BP/J-25	TC558	8P/J-35	UNIT
	PARAMETER	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SYMBOL	7,44			20	-	25	-	35	-	
twc	Write Cycle Time	15		13		15		15	-	
tcw	Chip Enable to End of Write	12	 		-	0	 _	0	-	
^t AS	Address Set Up Time .		<u> </u>	0	 	15	 	15		1
twp	Write Pulse Width	12	 	13		+	 	0	_	ns
twr	Write Recovery Time	0	<u> </u>	0	 - -	0	 	12	 	1
	Data Set Up Time	9		10	 	12	ļ- <u>-</u> -	0	 	1
tos	Data Hold Time	0		0		0	 	+	+	1
t _{DH}	Output Enable Time from WE	0		0		0		1 0	+	-
toew	Output Disable Time from WE	_	6		6	<u></u>	6		6	<u></u>

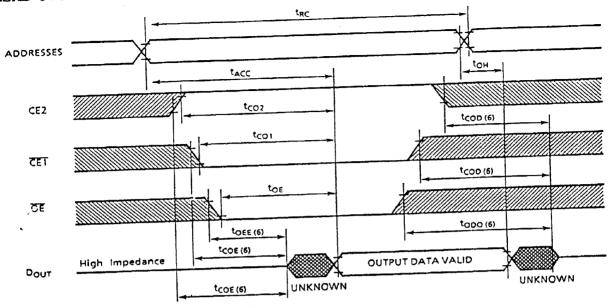
ACTEST CONDITIONS

Input Pulse Levels	3.0V/0.0V
Input Pulse Rise and Fall Time	3ns
Input Timing Measurement Reference Levels	2.2V/0.8V
Output Timing Measurement Reference	2.0V/0.8V
Levels Output Load	Fig. 1

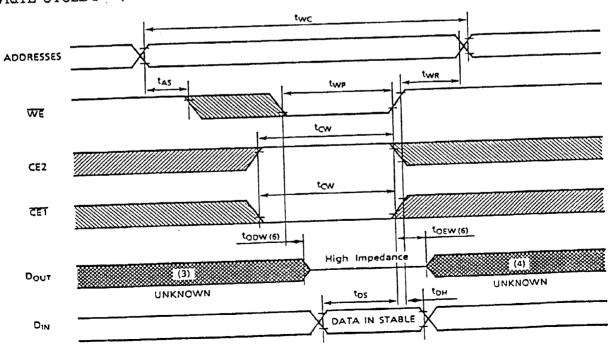


TIMING WAVEFORMS

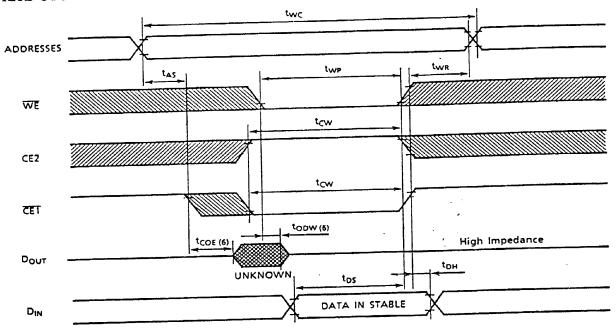
READ CYCLE (2)



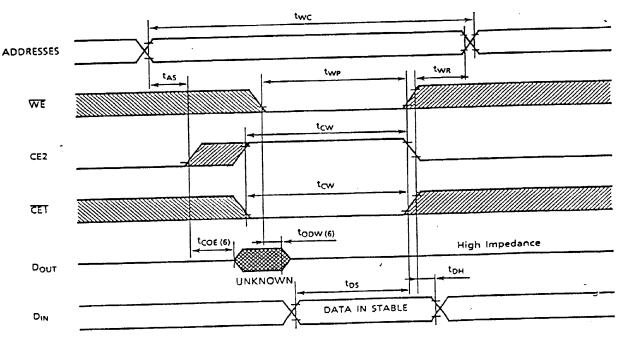
WRITE CYCLE 1 (5) (WE Controlled Write)



WRITE CYCLE 2 (5) (CEI Controlled Write)



WRITE CYLCE 3 (5) (CE2 Controlled Write)



- NOTES: 1. The operating temperature (Ta) is guaranteed with transverse air flow exceeding 400 linear feet per minute.
 - **2. WE** is High for Read Cycle.
 - Assuming that CE1 Low transition or CE2 High t ransi tion occurs coincident with or after WE Low transition, Outputs remain in a high impedance state.
 - 4. Assuming that CE1 High transition or CE2 Low transition occurs coincident with or prior to WE High transition, Outputs remain in a high impedance state.
 - Assuming that OE is High for Write Cycle, Outputs are in a high impedance state during this period.
 - These Parameters are specified as follows and measured by using the Ioad shown in Fig. 1.
 - (A) tCOE, tOEE, tOEW Output Enable Time
 - (B) tCOD, tODO, tODW Output Disable Time

